

**Francesco Pintacuda** received his graduate in Electronic Engineer at Palermo University in 2001. Since 2002 he has been worked in STMicroelectronics as power discrete transistor designer. The actual position is rad-hard design manager for power transistor inside the R&D Power & Discrete Group. In his job, he acquired experiences in radiation effect (Co60,X-ray, heavy ions) for space application, cosmic ray effect for avionics and automotive power application, and advanced reliability. Since 2016 he has research projects (*Characterization of Gate oxide of Silicon and SiC Power Mosfet by X-ray source -- Characterization of Silicon and SiC Power Device by atmospheric neutron and alpha particle*) with Physical and Chemistry department of Palermo University. Since 2020 he has research project with European avionics company to introduce the SiC power Mosfet in new electrical vehicles. He has research cooperation with IRT- Saint Exupery inside SICRET project. He is author or co-author of more than 10 of technical and conference papers.